PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = BENSAHEL
First Name = DANIEL

Application#	Patent#	Status	Date Filed	Title	Inventor Name
06042081	4263056	150	05/24/1979	METHOD FOR THE MANUFACTURE OF LIGHT EMITTING AND/OR PHOTODETECTIVE DIODES	BENSAHEL, DANIEL
06085948	4229237	150	10/18/1979	METHOD OF FABRICATION OF SEMICONDUCTOR COMPONENTS HAVING OPTOELECTRONIC CONVERSION PROPERTIES	BENSAHEL, DANIEL
06853906	4678538	250	04/21/1986	PROCESS FOR THE PRODUCTION OF AN INSULATING SUPPORT ON AN ORIENTED MONOCRYSTALLINE SILICON FILM WITH LOCALIZED DEFECTS	BENSAHEL, DANIEL
06882901	4725561	150	06/05/1986	PROCESS FOR THE PRODUCTION OF MUTUALLY ELECTRICALLY INSULATED MONOCRYSTALLINE SILICON ISLANDS USING LASER RECRYSTALLIZATION	BENSAHEL, DANIEL
07808745	5252181	150	12/17/1991	METHOD FOR CLEANING THE SURFACE OF A SUBSTRATE WITH PLASMA	BENSAHEL, DANIEL
07914380	Not Issued	161	07/15/1992	DEVICE FOR INJECTING A PRODUCT INTO AN ENCLOSED CHAMBER SUCH AS A REACTOR FOR MICROELECTRONICS	BENSAHEL, DANIEL
08797511	5876796	150	12/23/1996	PROCESS FOR SELECTIVELY DEPOSITING A REFRACTORY METAL SILICIDE ON SILICON, AND SILICON WAFER	BENSAHEL, DANIEL

				METALLIZED USING THIS PROCESS	
09217025	6117750	150	12/21/1998	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM OR SILICON ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON OR GERMANIUM, RESPECTIVELY	BENSAHEL, DANIEL
09403356	6372581	150	10/18/1999	PROCESS FOR NITRIDING THE GATE OXIDE LAYER OF A SEMICONDUCTOR DEVICE AND DEVICE OBTAINED	BENSAHEL, DANIEL
09403442	6255149	150	10/19/1999	PROCESS FOR RESTRICTING INTERDIFFUSION IN A SEMICONDUCTOR DEVICE WITH COMPOSITE SI/SIGE GATE	BENSAHEL, DANIEL
09540188	6399502	150	03/31/2000	PROCESS FOR FABRICATING A PLANAR HETEROSTRUCTURE	BENSAHEL, DANIEL
09659913	6429098	150	09/11/2000	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM OR SILICON ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON OR GERMANIUM, RESPECTIVELY, AND MULTILAYER PRODUCTS OBTAINED	BENSAHEL, DANIEL
09763532	6551698	150	04/04/2001	METHOD FOR TREATING A SILICON SUBSTRATE, BY NITRIDING, TO FORM A THIN INSULATING LAYER	BENSAHEL, DANIEL
09786996	6537370	150	03/09/2001	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON, AND PRODUCTS OBTAINED	BENSAHEL, DANIEL
09921642	6596555	150	08/03/2001	FORMING OF QUANTUM DOTS	BENSAHEL, DANIEL
10048719	6690027	150	06/13/2002	METHOD FOR MAKING A DEVICE COMPRISING LAYERS OF PLANES OF QUANTUM DOTS	BENSAHEL, DANIEL
10405075	Not	061	03/31/2003	STRAINED-CHANNEL	BENSAHEL,

	Issued			ISOLATED-GATE FIELD EFFECT TRANSISTOR, PROCESS FOR MAKING SAME AND RESULTING INTEGRATED CIRCUIT	DANIEL
10614675	Not Issued	071	07/07/2003	GROWTH OF A SINGLE-CRYSTAL REGION OF A III-V COMPOUND ON A SINGLE-CRYSTAL SILICON SUBSTRATE	BENSAHEL, DANIEL
10615259	Not Issued	090	07/09/2003	PROCESS FOR TRANSFERRING A LAYER OF STRAINED SEMICONDUCTOR MATERIAL	BENSAHEL, DANIEL
10744680	Not Issued	051	12/23/2003	METHOD FOR FORMING A LOCALIZED REGION OF A MATERIAL DIFFICULT TO ETCH	BENSAHEL, DANIEL
10815473	Not Issued	030	04/01/2004	METHOD OF FABRICATING A SEMICONDUCTOR DEVICE COMPRISING A GATE DIELECTRIC MADE OF HIGH DIELECTRIC PERMITTIVITY MATERIAL	BENSAHEL, DANIEL
10816214	Not Issued	030	04/01/2004	HETEROATOMIC SINGLE-CRYSTAL LAYERS	BENSAHEL, DANIEL
10882995	Not Issued	030	07/01/2004	PROCESS FOR FABRICATING STRAINED LAYERS OF SILICON OR OF A SILICON/GERMANIUM ALLOY	BENSAHEL, DANIEL
60445825	Not Issued	159	02/10/2003	PROCESS FOR TRANSFERRING A LAYER OF STRAINED SEMICONDUCTOR MATERIAL	BENSAHEL, DANIEL
60461656	Not Issued	159	04/09/2003	TERAHERTZ SOURCES AND DETECTORS BASED ON SILICON AND SILICON GERMANIUM ALLOYS AND METHOD OF MANUFACTURE	BENSAHEL, DANIEL

Inventor Search Completed: No Records to Display.

Search Another: Inventor

Last Name	First Name	
Bensahel	Daniel	Search

To go back use Back button on your browser toolbar.

Examiner's Notes

James H. Morris
Tel (617) 738-3500

10/614,675

117(54,89,101

Written Restriction Requested on 1/4/05

5 (single (w) crystal? or mono crystal?) (6a) (wafer# or substrate#)
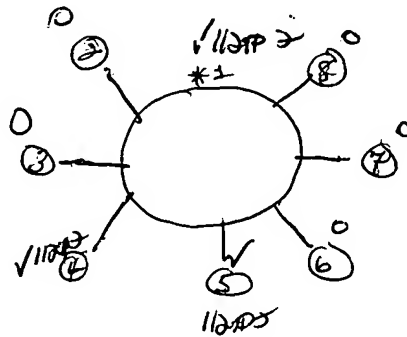5 (III (w) V) (4a) (compound#)
4 5 (single (w) crystal?) (8a) (region# or area#)
5 (Ge or germanium (4a) layer) (10a) (single (w) crystal? or mono (w) crystal?)
5 (etch?) (8a) (germanium (4a) layer or Ge (4a) layer)
5 (crystallographic (w) plane)

112 ¶ 2 Rej

112 ¶ 2 Rej

Claim 1, lines 5-6, "... bottom... (No antecedence)

Claim 4, line 2, "... germanium allow..." (No antecedence)

Claim 5, line 3, "... shape of... " (No antecedence)